

Abstract

A method for plasma treatment etches an SiC layer with an increased etching rate and enhanced selectivities of SiC with respect to SiO₂ and an organic layer. An etching gas is converted into plasma to etch SiC. The etching gas may include CHF₃; CHF₃ and N₂, for example, a mixed gas of CHF₃, N₂ and Ar; or a material having C, H and F and a material having N but without any material having O.

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